

低功耗 RS-485 线路驱动器和接收器对

1 特性

- 专为通过长电缆进行高速多点数据传输而设计
- 以低至 30ns 的脉冲持续时间运行
- 低电源电流：5 mA (最大值)
- 符合或超出 ANSI 标准 RS-485 和 ISO 8482:1987(E) 的要求
- 用于合用总线的三态输出
- -7V 至 12V 的共模电压范围
- 过热关断保护可避免因总线争用导致的驱动器损坏
- 正负输出电流限制
- 引脚与 SN75ALS180 兼容

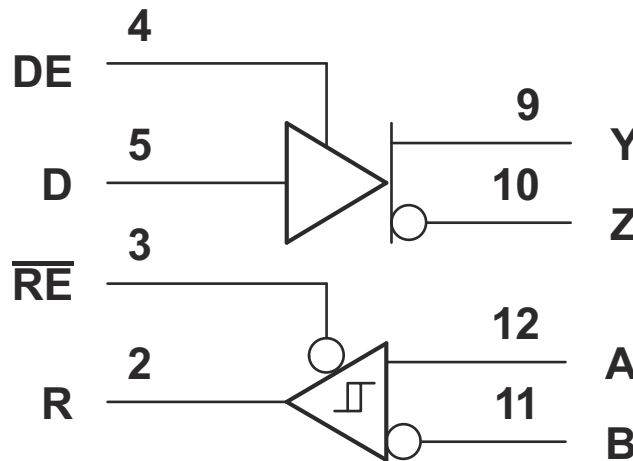
2 说明

SN55LBC180、SN65LBC180 和 SN75LBC180 差分驱动器和接收器对是单片集成电路，设计用于通过具有传输线特性的长电缆进行双向数据通信。它们是平衡或差分电压模式器件，符合或超过行业标准 ANSI RS-485 和 ISO 8482:1987(E) 的要求。这些器件采用 TI 专用 LinBiCMOS™ 进行设计，具有 CMOS 的低功耗以及同一电路中双极晶体管的精度和稳健性。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 (标称值)
SN75LBC180	N (PDIP)	19.3 mm x 63.5 mm
	D (SOIC)	8.65mm x 3.91mm
SN65LBC180	RSA (QFN)	4mm x 4mm
SN55LBC180	RSA (QFN)	4mm x 4mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



逻辑图 (正逻辑)



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3 说明 (续)

SN55LBC180、SN65LBC180 和 SN75LBC180 将差分线路驱动器和接收器与三态输出相结合，并采用 5V 单电源供电。驱动器和接收器分别具有高电平有效和低电平有效使能端，它们可以在外部连接在一起以用作方向控制。驱动器差分输出和接收器差分输入连接到单独的端子以实现全双工工作，并且旨在为总线提供最小负载，无论是禁用还是断电 ($V_{CC} = 0$)。这些器件具有宽共模电压范围，使其适用于点对点或多点数据总线应用。

这些器件还提供正负输出电流限制和热关断功能，避免出现线路故障状况。线路驱动器在结温约为 172°C 时关闭。

SN75LBC180 可在 0°C 至 70°C 的商业温度范围内运行。SN65LBC180 可在 -40°C 至 85°C 的工业温度范围内运行。

SN55LBC180 的军用级温度范围为 -55°C 至 125°C。

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision H (June 2022) to Revision I (October 2022)	Page
• Changed RSA (QFN) values in the <i>Thermal Information Table</i>	6

Changes from Revision G (April 2009) to Revision H (June 2022)	Page
• 将“订购信息”表更改为封装信息表.....	1
• Added the <i>Pin Configuration and Functions</i>	4
• Added the <i>Thermal Information Table</i>	6
• Fixed the typo in the unit for the Receiver enable I_{IH} to change the unit from A to μ A.....	7
• Updated 图 6-1, 图 6-2, and 图 6-3, limiting the x-axis to a maximum of 70 mA driver output current.....	9
• Updated 图 9-1 to remove legacy terminology	17

Changes from Revision F (March 2009) to Revision G (April 2009)	Page
• Added 3 ESD rows to the <i>Absolute Maximum Ratings</i>	5

Changes from Revision E (February 2006) to Revision F (March 2009)	Page
• 将数据表标题中的“差分”更改为“RS-485”	1
• 添加了器件型号 SN55LBC180.....	1
• 将两个更改为这些	1
• 添加了“订购信息”表.....	1
• 更新了说明(续)部分.....	2
• 更改了功能表并将其从首页移到说明(续)部分.....	2
• Deleted condition, moved cross reference.....	5
• Added all symbols in text that were not appearing in the PDF.....	5
• Deleted T_A row from the <i>Absolute Maximum Ratings</i>	5
• Added the last column to <i>Dissipation Rating Table</i>	5
• Added a row to T_A in the <i>Recommended Operating Conditions</i> for SN55LBC180.....	5
• Added SN55LB180 to the $ V_{OD} $ row.....	6
• Change: moved 5 max values to the min column (-1.5, -50, -100, -0.8, -0.8).....	7
• Added the <i>Switching Characteristics: SN55LBC180</i> table	8
• Changed moved schematics to the Typical Characteristics section.....	16

5 Pin Configuration and Functions

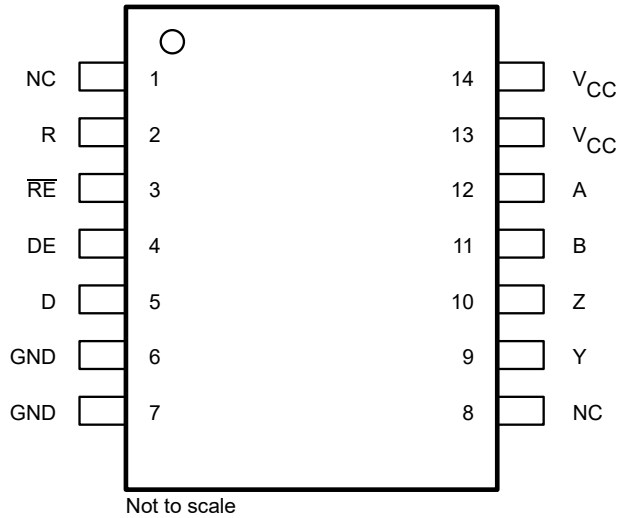


图 5-1. D OR N Package (SOIC)
(Top View)

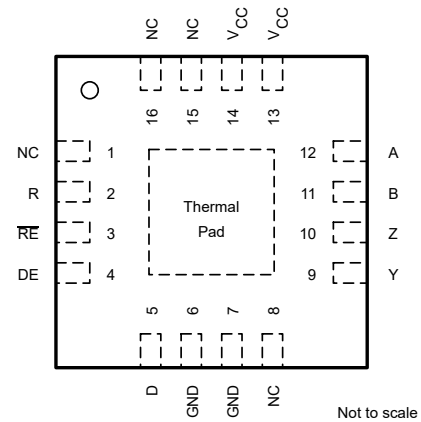


图 5-2. RSA Package (QFN)
(Top View)

表 5-1. Pin Functions

PIN NAME	PIN NO		TYPE ⁽¹⁾	DESCRIPTION
	D Or N	RSA		
NC	1	1	NC	No internal connection
R	2	2	O	Receiver output
RE	3	3	I	Receiver enable input. Active low.
DE	4	4	I	Driver enable input. Active high
D	5	5	I	Driver input pin
GND	6, 7	6, 7	G	Ground connection. Pins 6 and 7 are connected together internally.
NC	8	8	NC	No internal connection
Y	9	9	O	Bus output port (complementary to Z)
Z	10	10	O	Bus output port (complementary to Y)
B	11	11	I	Bus input port (complementary to A)
A	12	12	I	Bus input port (complementary to B)
V _{CC}	13, 14	13, 14	P	Supply input pins. Pins 13 and 14 are connected together internally.
NC	N/A	15, 16	NC	No internal connection

(1) Signal Types: I = Input, O = Output, P= Power input,

6 Specifications

6.1 Absolute Maximum Ratings

See note (1)

			UNIT	
V _{CC}	Supply voltage range (2)	- 0.3 to 7	V	
V _{BUS}	Bus voltage range (A, B, Y, Z)(2)	- 10 to 15	V	
	Voltage range at D, R, DE, RE (2)	- 0.3 to V _{CC} + 0.5	V	
	Continuous total power dissipation(3)	Internally limited		
	Total power dissipation	See Dissipation Rating Table		
T _{stg}	Storage temperature range	- 65 to 150	°C	
I _O	Receiver output current range	- 50 to 50	mA	
ESD	Electrostatic discharge	HBM (Human Body Model) EIA/JESD22-A114	±4	kV
		MM (Machine Model) EIA/JESD22-A115	400	V
		CDM (Charge Device Model) EIA/JESD22-C101	1.5	kV

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to GND.
- (3) The maximum operating junction temperature is internally limited. Use the dissipation rating table to operate below this temperature.

6.2 Dissipation Rating Table

PACKAGE(1)	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	—
N	1150 mW	9.2 mW/°C	736 mW	598 mW	—
RSA	3333 mW	26.67 mW/°C	2133 mW	1733 mW	400 mW

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT	
V _{CC}	Supply voltage	4.75	5	5.25	V	
V _{IH}	High-level input voltage	D, DE, and RE		2	V	
V _{IL}	Low-level input voltage	D, DE, and RE		0.8	V	
V _{ID}	Differential input voltage			- 6(1)	6	V
V _O , V _I , or V _{IC}	Voltage at any bus terminal (separately or common mode)	A, B, Y, or Z		- 7(1)	12	V
I _{OH}	High-level output current	Y or Z		- 60	mA	
		R		- 8		
I _{OL}	Low-level output current	Y or Z		60	mA	
		R		8		
T _A	Operating free-air temperature	SN55LBC180		- 55	125	°C
		SN65LBC180		- 40	85	
		SN75LBC180		0	70	

- (1) The algebraic convention where the least positive (more negative) limit is designated minimum, is used in this data sheet for the differential input voltage, voltage at any bus terminal, operating temperature, input threshold voltage, and common-mode output voltage.

6.4 Thermal Information Table

THERMAL METRIC ⁽¹⁾		D (SOIC)	N (PDIP)	RSA (QFN)	UNIT
		14 Pins	14 Pins	16 Pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	93.2	53.4	38.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	47.5	40.0	35.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	49.4	33.2	17.5	°C/W
ψ_{JT}	Junction-to-top characterization parameter	11.2	19.0	1.1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	48.9	32.9	17.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	7.9	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

6.5 Driver Section

6.5.1 Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IK}	Input clamp voltage	$I_I = -18 \text{ mA}$				- 1.5	V
$ V_{OD} $	Differential output voltage magnitude ⁽²⁾	$R_L = 54 \Omega$, See 图 7-1	SN55LBC180	1	2.5	5	V
			SN65LBC180	1.1	2.5	5	
			SN75LBC180	1.5	2.5	5	
		$R_L = 60 \Omega$, See 图 7-2	SN55LBC180	1	2.5	5	
			SN65LBC180	1.1	2	5	
			SN75LBC180	1.5	2	5	
$\Delta V_{OD} $	Change in magnitude of differential output voltage ⁽³⁾	See 图 7-1 and 图 7-2				±0.2	V
V_{OC}	Common-mode output voltage			1	2.5	3	V
$\Delta V_{OC} $	Change in magnitude of common-mode output voltage ⁽³⁾	$R_L = 54 \Omega$,	See 图 7-1			±0.2	V
I_O	Output current with power off	$V_{CC} = 0$,	$V_O = -7 \text{ V to } 12 \text{ V}$			±100	μA
I_{OZ}	High-impedance-state output current	$V_O = -7 \text{ V to } 12 \text{ V}$				±100	μA
I_{IH}	High-level input current	$V_I = 2.4 \text{ V}$				100	μA
I_{IL}	Low-level input current	$V_I = 0.4 \text{ V}$				100	μA
I_{OS}	Short-circuit output current	$-7 \text{ V} \leq V_O \leq 12 \text{ V}$				±250	mA
I_{CC}	Supply current	Receiver disabled	Outputs enabled			5	mA
			Outputs disabled			3	

(1) All typical values are at $V_{CC} = 5 \text{ V}$ and $T_A = 25^\circ\text{C}$.

(2) The minimum V_{OD} specification may not fully comply with ANSI RS-485 at operating temperatures below 0°C . System designers should take the possibly lower output signal into account in determining the maximum signal-transmission distance.

(3) $\Delta |V_{OD}|$ and $\Delta |V_{OC}|$ are the changes in the steady-state magnitude of V_{OD} and V_{OC} , respectively, that occur when the input is changed from a high level to a low level.

6.5.2 Switching Characteristics

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{d(OD)}$	Differential output delay time	$R_L = 54\ \Omega$,	See 图 7-3	7	12	18	ns
$t_{t(OD)}$	Differential output transition time			5	10	20	ns
t_{PZH}	Output enable time to high level	$R_L = 110\ \Omega$,	See 图 7-4			35	ns
t_{PZL}	Output enable time to low level	$R_L = 110\ \Omega$,	See 图 7-5			35	ns
t_{PHZ}	Output disable time from high level	$R_L = 110\ \Omega$,	See 图 7-4			50	ns
t_{PLZ}	Output disable time from low level	$R_L = 110\ \Omega$,	See 图 7-5			35	ns

6.5.3 Switching Characteristics: SN55LBC180

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{d(OD)}$	Differential output delay time	$R_L = 54\ \Omega$,	See 图 7-3		15		ns
$t_{t(OD)}$	Differential output transition time				21		ns
t_{PZH}	Output enable time to high level	$R_L = 110\ \Omega$,	See 图 7-4		32		ns
t_{PHZ}	Output disable time from high level				55		
t_{PZL}	Output enable time to low level	$R_L = 110\ \Omega$,	See 图 7-5		32		ns
t_{PLZ}	Output disable time from low level				20		

6.6 Receiver Section

6.6.1 Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	$I_O = -8\text{ mA}$				0.2	V
V_{IT-}	Negative-going input threshold voltage	$I_O = 8\text{ mA}$		-0.2			V
V_{hys}	Hysteresis voltage ($V_{IT+} - V_{IT-}$)				45		mV
V_{IK}	Enable-input clamp voltage	$I_I = -18\text{ mA}$		-1.5			V
V_{OH}	High-level output voltage	$V_{ID} = 200\text{ mV}$,	$I_{OH} = -8\text{ mA}$	3.5	4.5		V
V_{OL}	Low-level output voltage	$V_{ID} = -200\text{ mV}$,	$I_{OL} = 8\text{ mA}$		0.3	0.5	V
I_{OZ}	High-impedance-state output current	$V_O = 0\text{ V to }V_{CC}$				± 20	$\mu\text{ A}$
I_{IH}	High-level enable-input current	$V_{IH} = 2.4\text{ V}$		-50			$\mu\text{ A}$
I_{IL}	Low-level enable-input current	$V_{IL} = 0.4\text{ V}$		-100			$\mu\text{ A}$
I_I	Bus input current	$V_I = 12\text{ V}$, $V_{CC} = 5\text{ V}$,	Other input at 0 V		0.7	1	mA
		$V_I = 12\text{ V}$, $V_{CC} = 0\text{ V}$,	Other input at 0 V		0.8	1	
		$V_I = -7\text{ V}$, $V_{CC} = 5\text{ V}$,	Other input at 0 V	-0.8	-0.5		
		$V_I = -7\text{ V}$, $V_{CC} = 0\text{ V}$,	Other input at 0 V	-0.8	-0.5		
I_{CC}	Supply current	Driver disabled	Outputs enabled			5	mA
			Outputs disabled			3	

6.6.2 Switching Characteristics

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PHL} Propagation delay time, high- to low-level output	$V_{ID} = -1.5\text{ V to }1.5\text{ V}$, See 图 7-6	11	22	33	ns
t_{PLH} Propagation delay time, low- to high-level output		11	22	33	ns
$t_{sk(p)}$ Pulse skew ($ t_{PHL} - t_{PLH} $)			3	6	ns
t_t Transition time			5	8	ns
t_{PZH} Output enable time to high level	See 图 7-7			35	ns
t_{PZL} Output enable time to low level				30	ns
t_{PHZ} Output disable time from high level				35	ns
t_{PLZ} Output disable time from low level				30	ns

6.6.3 Switching Characteristics: SN55LBC180

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PHL} Propagation delay time, high- to low-level output	$V_{ID} = -1.5\text{ V to }1.5\text{ V}$, See 图 7-6		26		ns
t_{PLH} Propagation delay time, low- to high-level output			23		ns
$t_{sk(p)}$ Pulse skew ($ t_{PHL} - t_{PLH} $)			3		ns
$t_{sk(p)t}$ Transition time			4		ns
t_{PZH} Output enable time to high level	See 图 7-4		30		ns
t_{PHZ} Output disable time from high level			26		ns
t_{PZL} Output enable time to low level			30		ns
t_{PLZ} Output disable time from low level			30		ns

6.7 Typical Characteristics

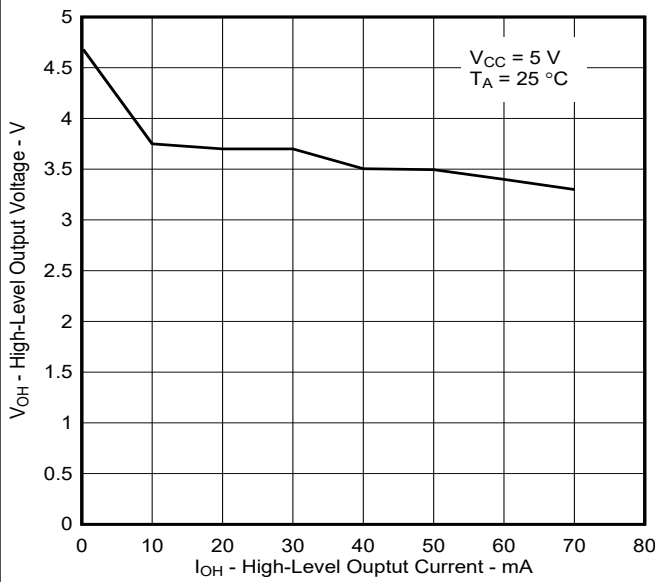


图 6-1. Driver High-Level Output Voltage vs High-Level Output Current

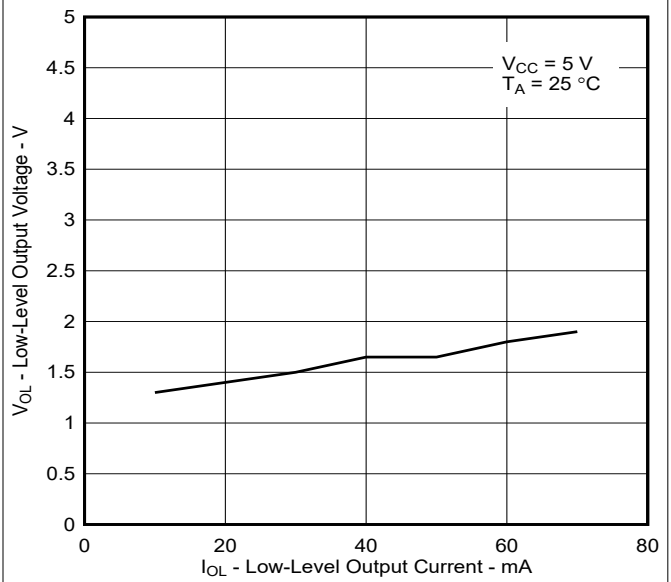


图 6-2. Driver Low-Level Output Voltage vs Low-Level Output Current

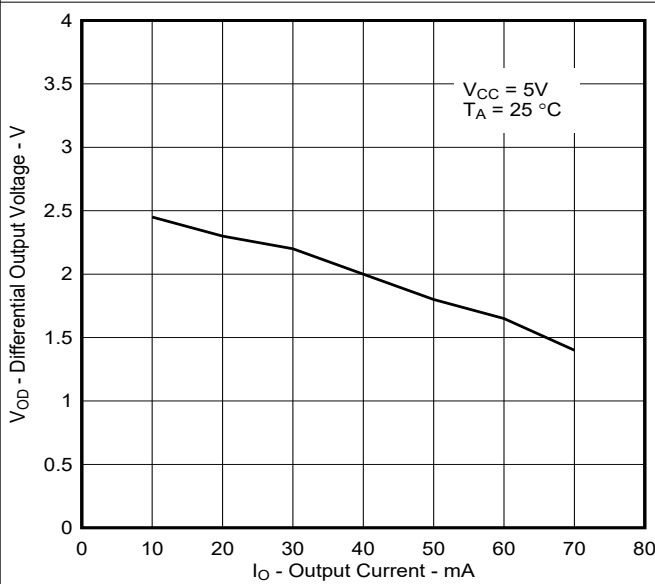


图 6-3. Driver Differential Output Voltage vs Output Current

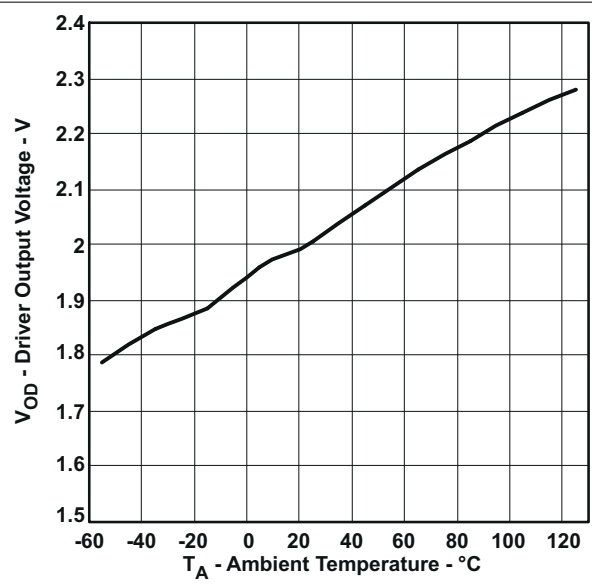


图 6-4. Driver Differential Output Voltage vs Free-Air Temperature

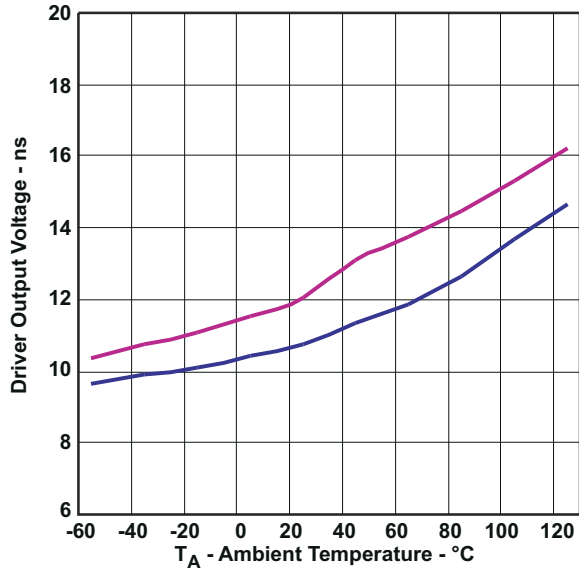


图 6-5. Driver Differential Delay Times vs Free-Air Temperature

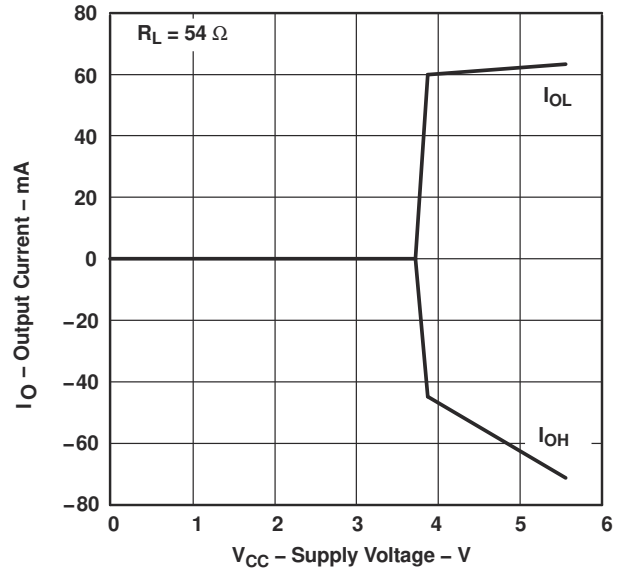


图 6-6. Driver Output Current vs Supply Voltage

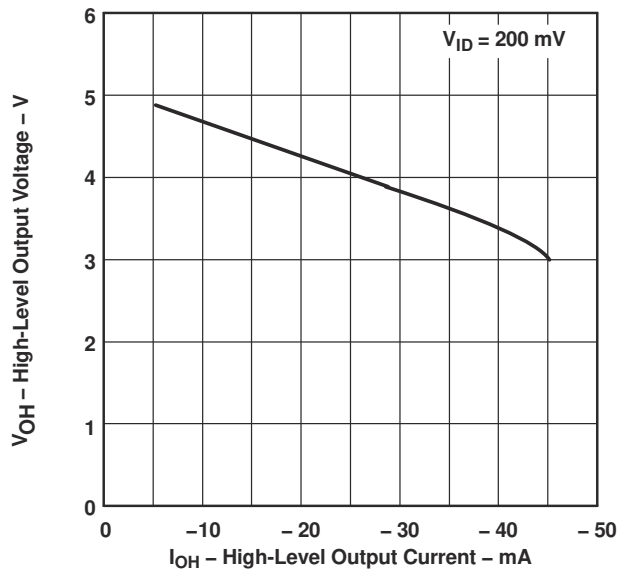


图 6-7. Receiver High-Level Output Voltage vs High-Level Output Current

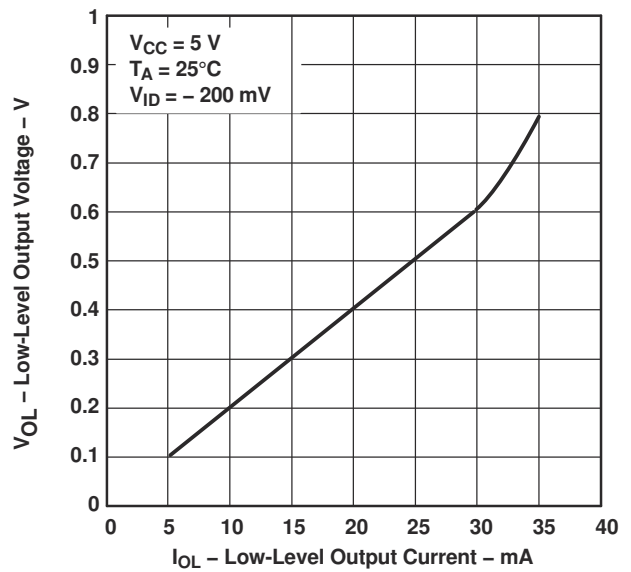


图 6-8. Receiver Low-Level Output Voltage vs Low-Level Output Current

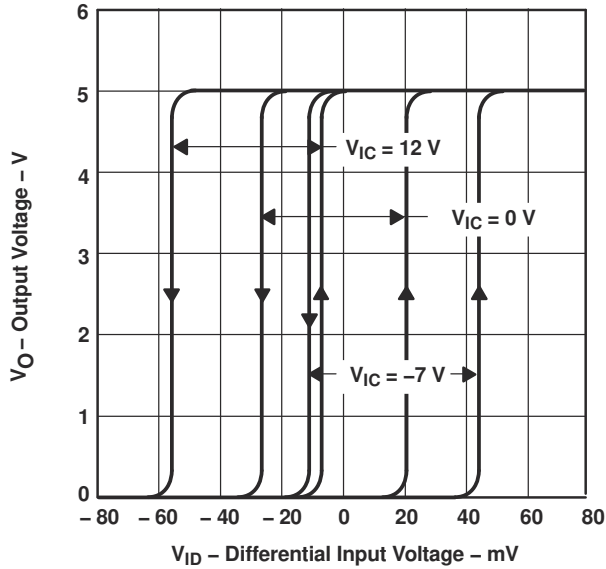


图 6-9. Receiver Output Voltage vs Differential Input Voltage

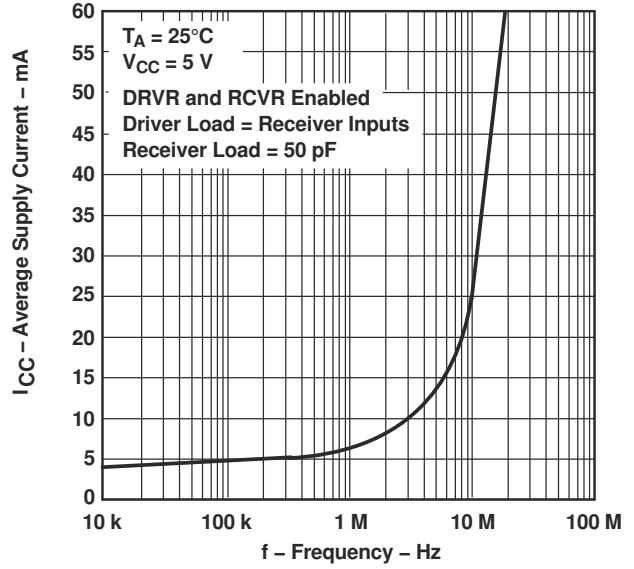


图 6-10. Average Supply Current vs Frequency

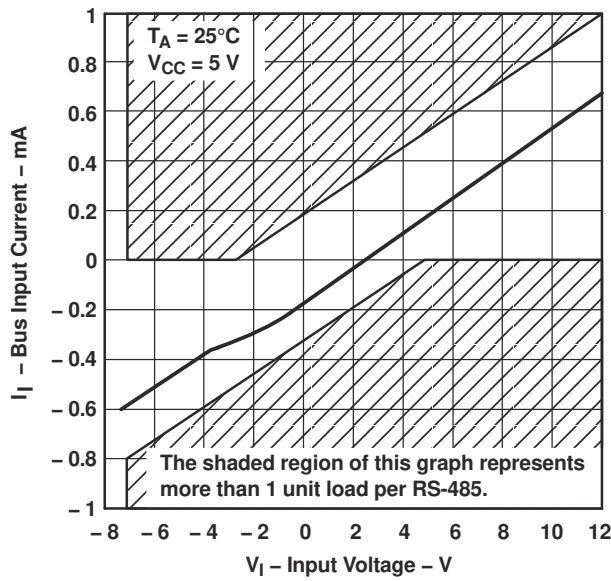


图 6-11. Receiver Bus Input Current vs Input Voltage (Complementary Input at 0 V)

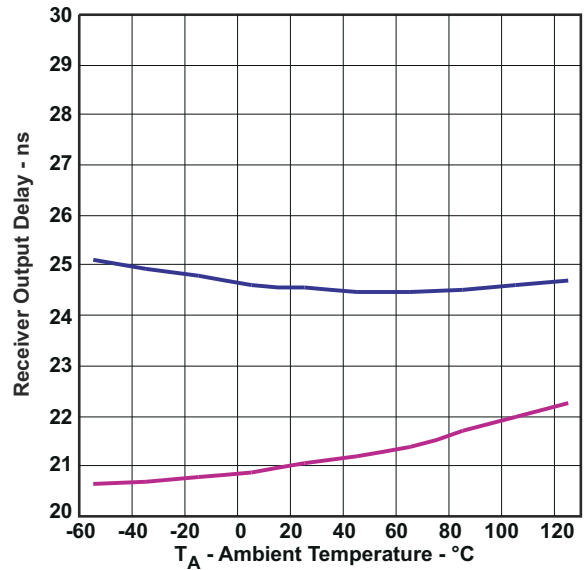


图 6-12. Receiver Propagation DELAY T_I vs Free-Air Temperature

7 Parameter Measurement Information

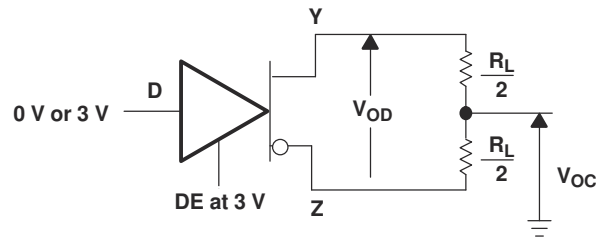


图 7-1. Differential and Common-Mode Output Voltages

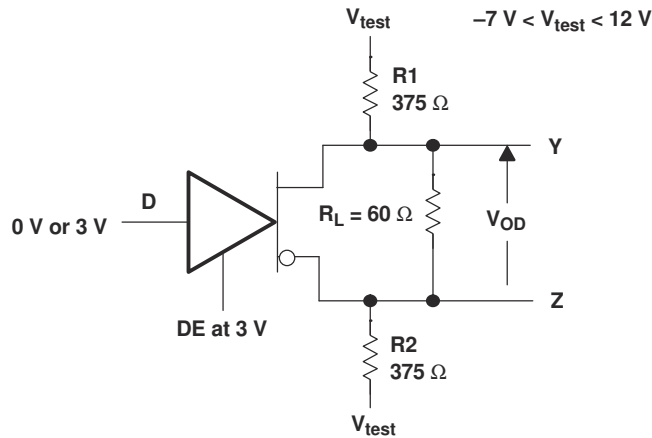
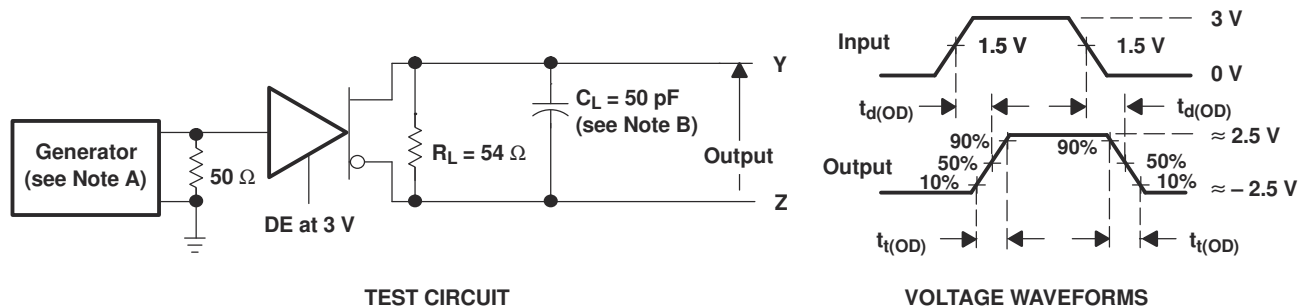


图 7-2. Driver V_{OD} Test Circuit



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR > 1 MHz, 50% duty cycle, $t_r \leq 6$ ns, $t_f \leq 6$ ns, $Z_O = 50 \Omega$.
 B. C_L includes probe and jig capacitance.

图 7-3. Driver Test Circuit and Differential Output Delay and Transition Time Voltage Waveforms

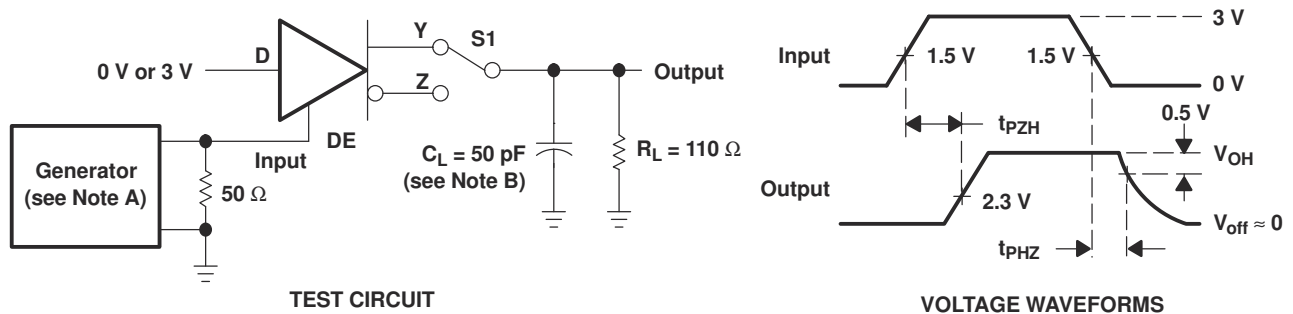
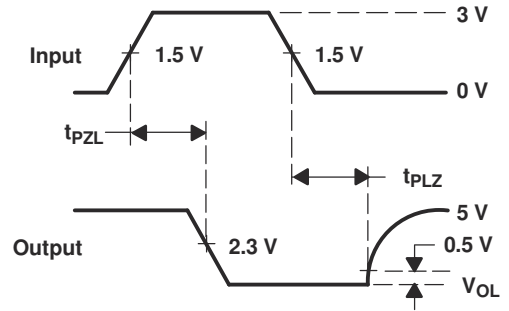
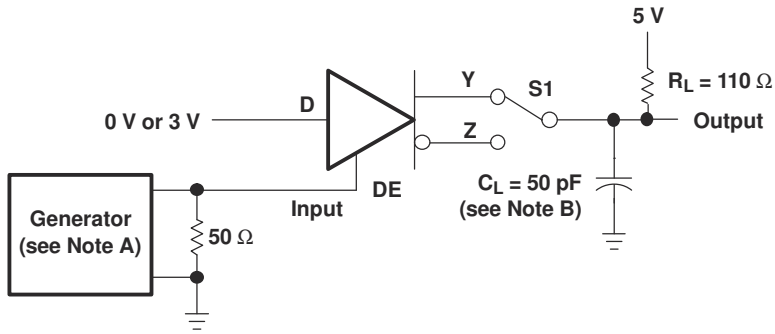


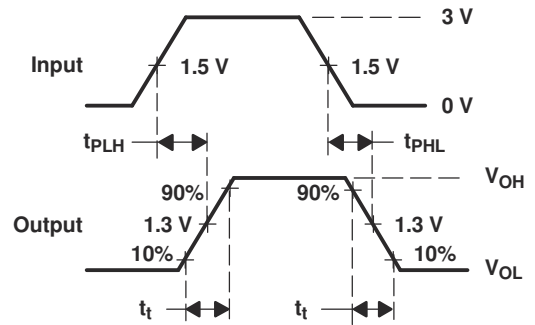
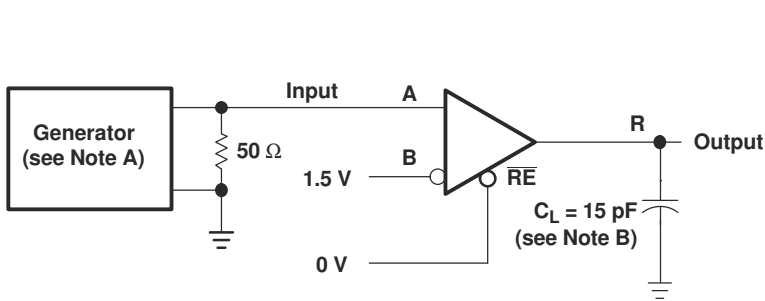
图 7-4. Driver Test Circuit and Enable and Disable Time Waveforms



TEST CIRCUIT

VOLTAGE WAVEFORMS

图 7-5. Driver Test Circuit and Enable and Disable Time Voltage Waveforms

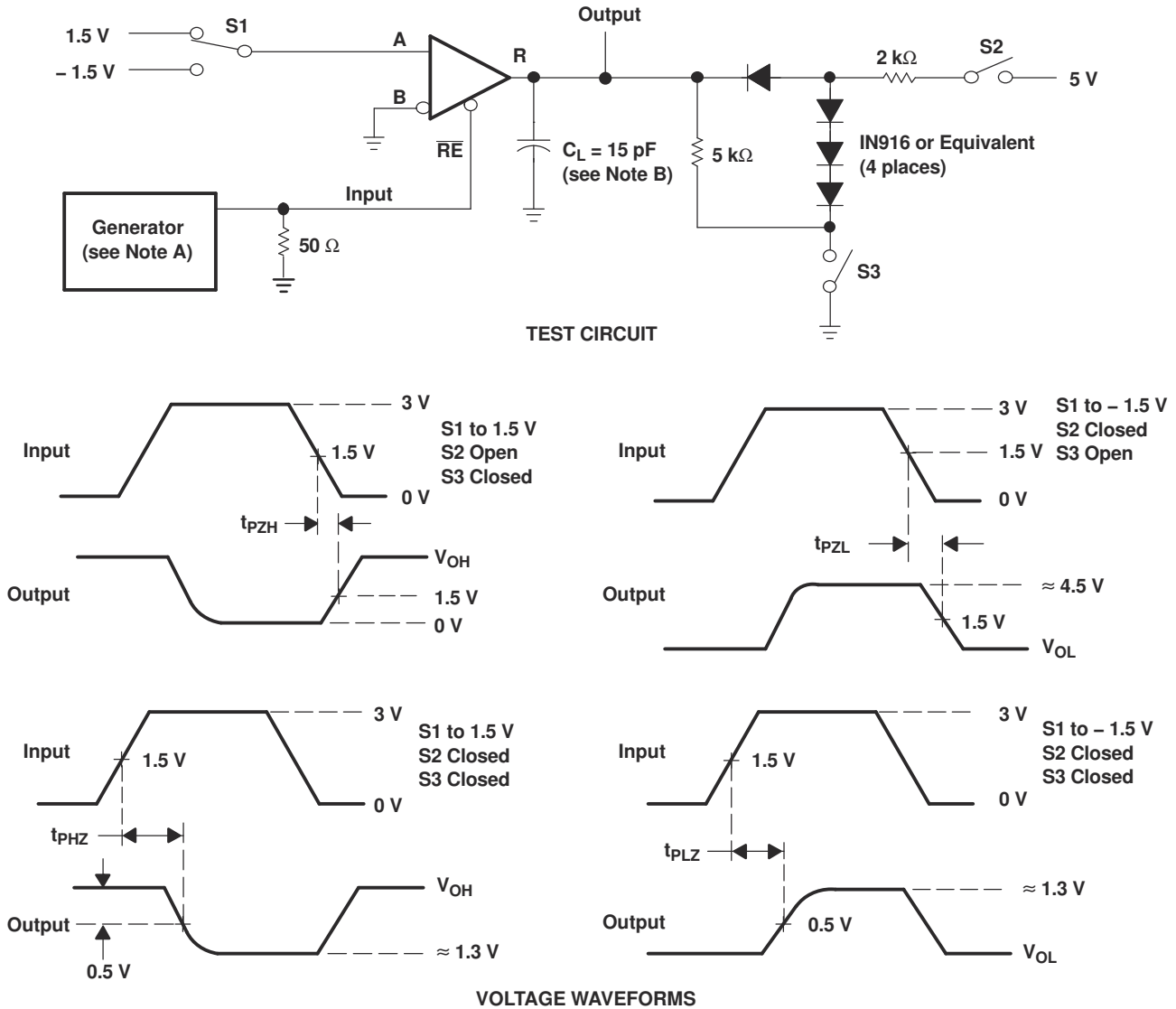


TEST CIRCUIT

VOLTAGE WAVEFORMS

- NOTES: A. The input pulse is supplied by a generator having the following characteristics: $PRR \leq 1 \text{ MHz}$, 50% duty cycle, $t_r \leq 6 \text{ ns}$, $t_f \leq 6 \text{ ns}$, $Z_O = 50 \Omega$.
 B. C_L includes probe and jig capacitance.

图 7-6. Receiver Test Circuit and Propagation Delay Time Voltage Waveforms



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: $PRR \leq 1$ MHz, 50% duty cycle, $t_r \leq 6$ ns, $t_f \leq 6$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.

图 7-7. Receiver Output Enable and Disable Times

8 Detailed Description

8.1 Function Tables

表 8-1. DRIVER

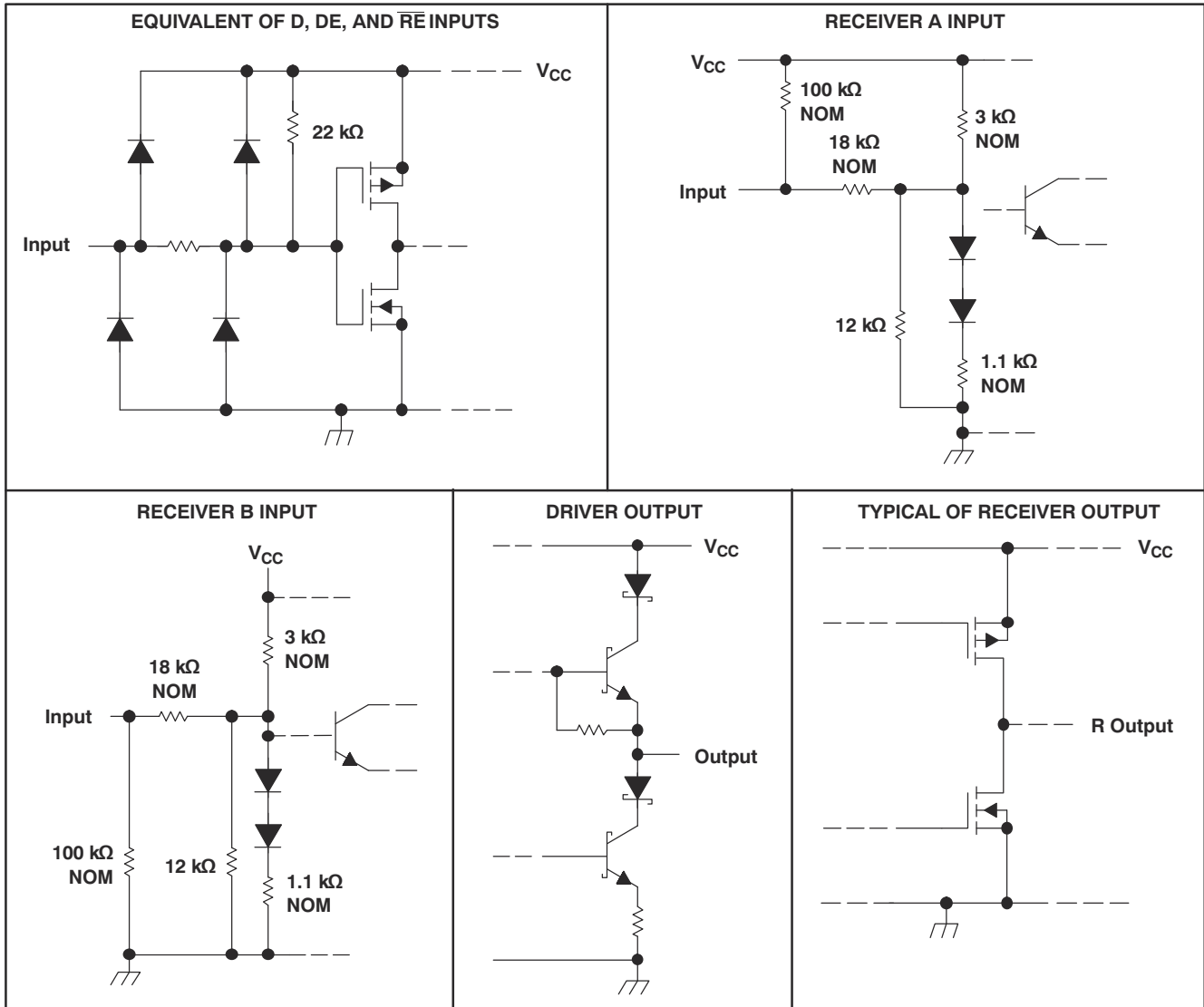
INPUT D ⁽¹⁾	ENABLE DE	OUTPUTS	
		Y	Z
H	H	H	L
L	H	L	H
X	L	Z	Z

(1) H = high level, L = low level, ? = Indeterminate, X = irrelevant,
Z = high impedance (off)

表 8-2. RECEIVER

DIFFERENTIAL INPUTS A - B	ENABLE RE	OUTPUT R	
		Y	Z
$V_{ID} \geq 0.2 V$	L	H	
$-0.2 V < V_{ID} < 0.2 V$	L	?	
$V_{ID} \leq -0.2 V$	L	L	
X	H	Z	
Open circuit	L	H	

8.2 Schematics of Inputs and Outputs



9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

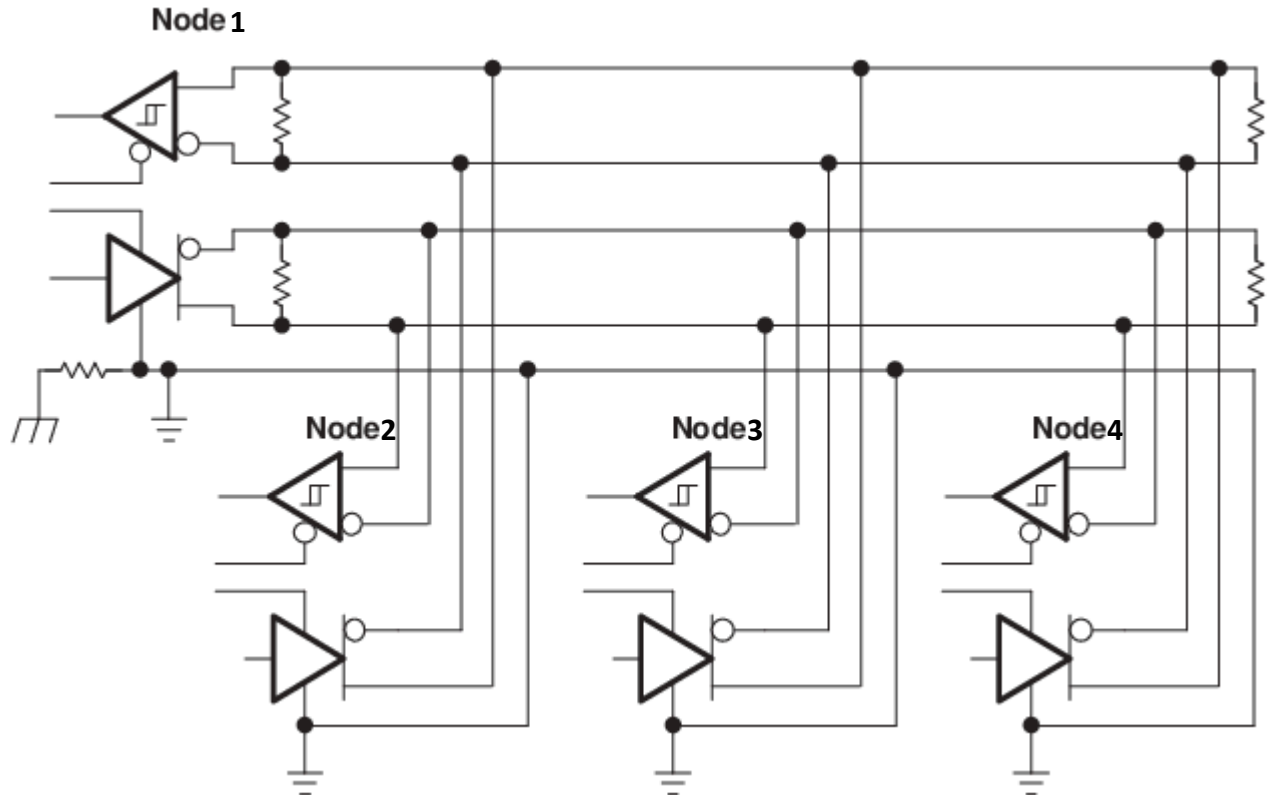


图 9-1. Full Duplex Application Circuit

10 Device and Documentation Support

10.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.2 支持资源

[TI E2E™ 支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

10.3 商标

LinBiCMOS™ is a trademark of Texas Instruments.

TI E2E™ is a trademark of Texas Instruments.

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10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN55LBC180RSAR	Active	Production	QFN (RSA) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	SN55 LBC180
SN55LBC180RSAR.A	Active	Production	QFN (RSA) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	SN55 LBC180
SN55LBC180RSARG4	Active	Production	QFN (RSA) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	SN55 LBC180
SN55LBC180RSARG4.A	Active	Production	QFN (RSA) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	SN55 LBC180
SN65LBC180DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB180
SN65LBC180DR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB180
SN65LBC180DRG4	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB180
SN65LBC180N	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	SN65LBC180N
SN65LBC180N.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	SN65LBC180N
SN65LBC180RSAR	Active	Production	QFN (RSA) 16	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 85	BL180
SN65LBC180RSAR.A	Active	Production	QFN (RSA) 16	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 85	BL180
SN75LBC180N	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	SN75LBC180N
SN75LBC180N.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	SN75LBC180N

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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OTHER QUALIFIED VERSIONS OF SN55LBC180, SN75LBC180 :

- Catalog : [SN75LBC180](#)
- Military : [SN55LBC180](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN55LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN55LBC180RSARG4	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN65LBC180DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN55LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0
SN55LBC180RSARG4	QFN	RSA	16	3000	367.0	367.0	35.0
SN65LBC180DR	SOIC	D	14	2500	340.5	336.1	32.0
SN65LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65LBC180N	N	PDIP	14	25	506	13.97	11230	4.32
SN65LBC180N.A	N	PDIP	14	25	506	13.97	11230	4.32
SN75LBC180N	N	PDIP	14	25	506	13.97	11230	4.32
SN75LBC180N.A	N	PDIP	14	25	506	13.97	11230	4.32

D0014A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

EXAMPLE BOARD LAYOUT

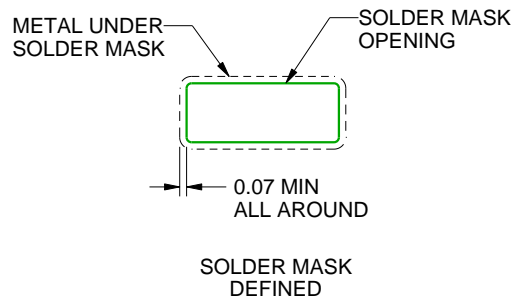
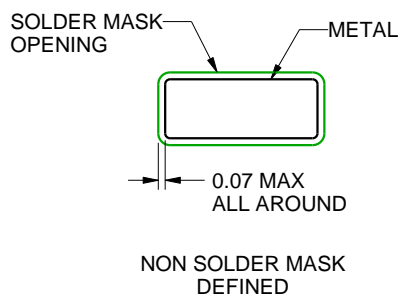
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

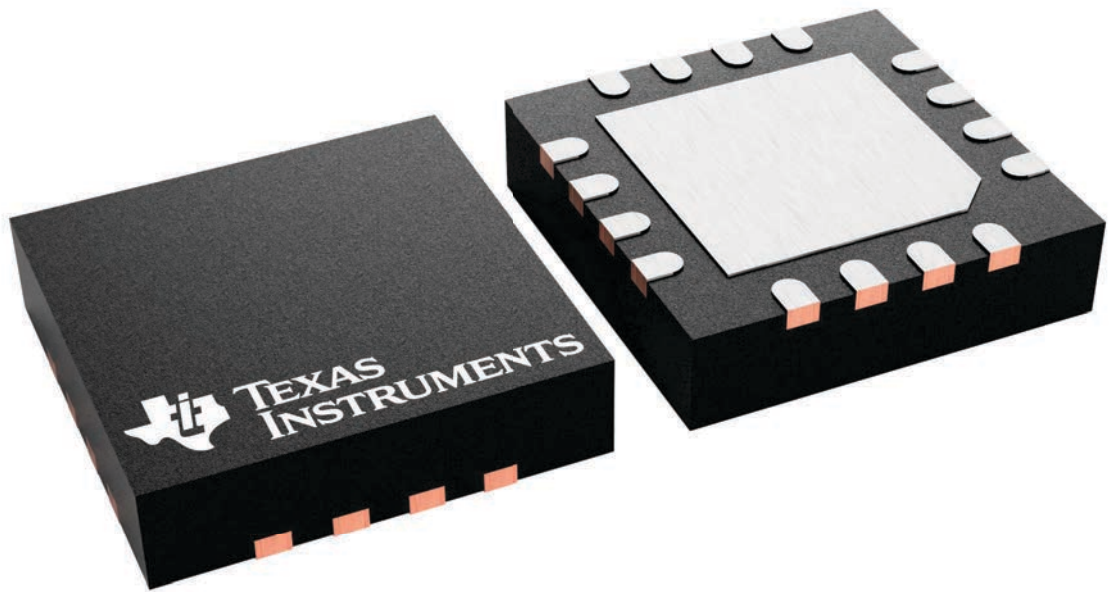
RSA 16

VQFN - 1 mm max height

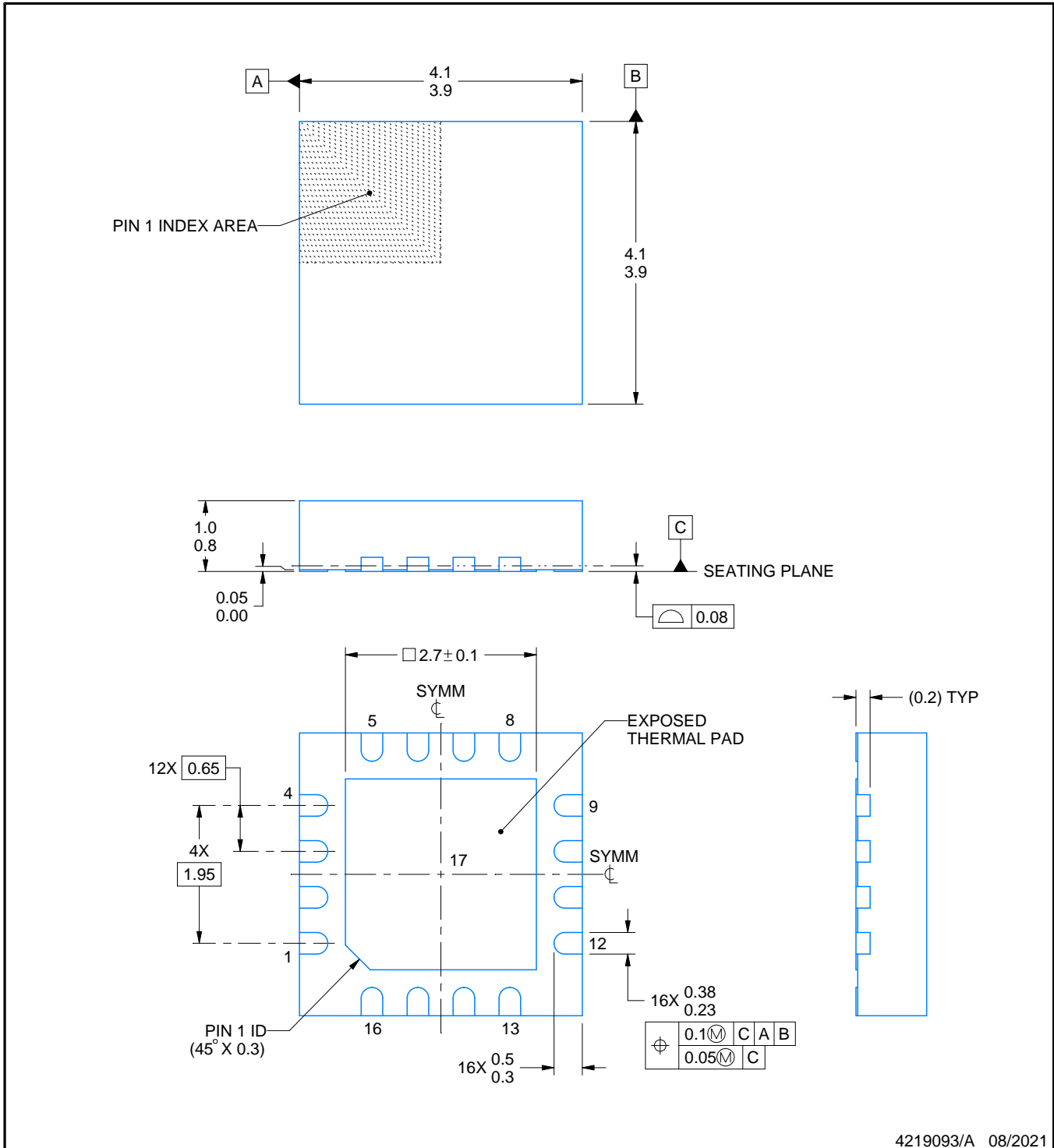
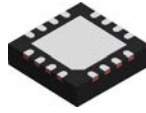
4 x 4, 0.65 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4230969/A



4219093/A 08/2021

NOTES:

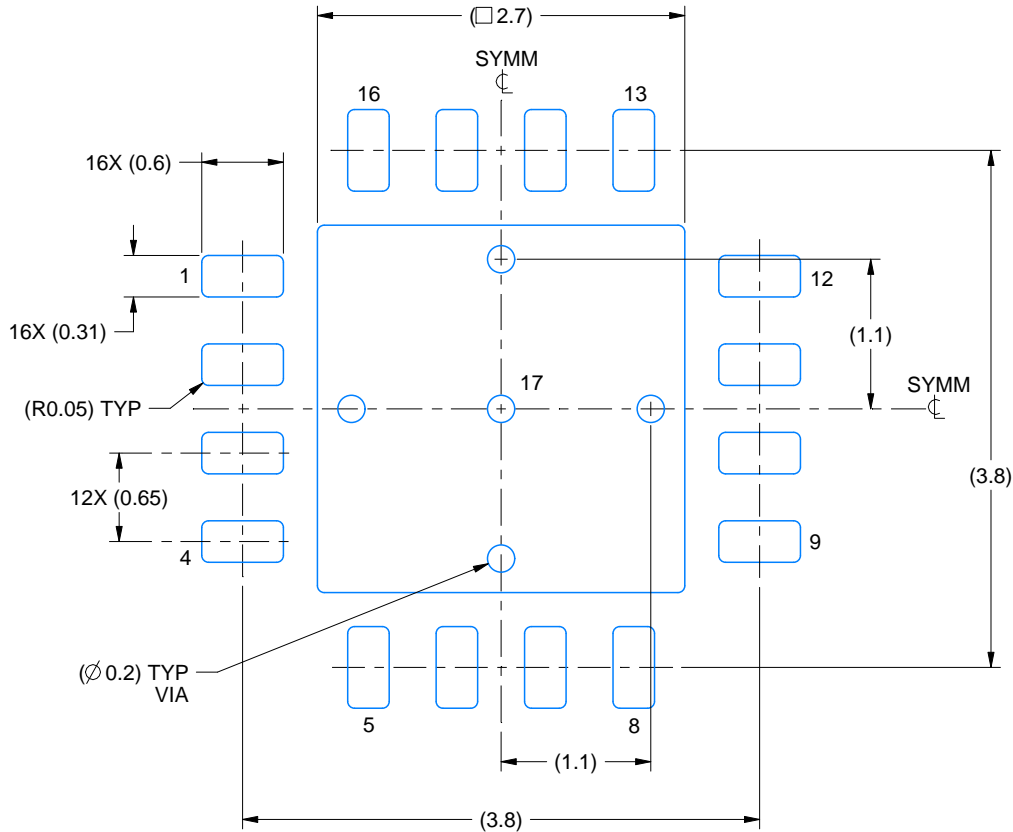
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
4. Reference JEDEC registration MO-220.

EXAMPLE BOARD LAYOUT

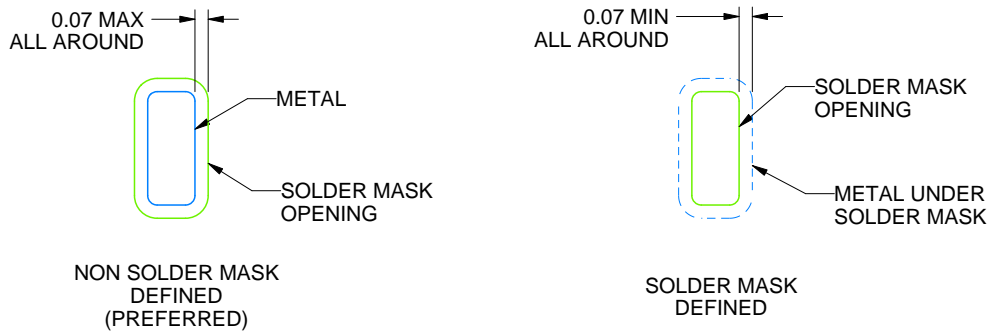
RSA0016B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4219093/A 08/2021

NOTES: (continued)

5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
6. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

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最后更新日期：2025 年 10 月